

650 V Power SiC Gen 3 Merged PIN Schottky Diode, 6 A



LINKS TO ADDITIONAL RESOURCES





PRIMARY CHARACTERISTICS					
I _F	6 A				
V_R	650 V				
V _F at I _F at 25 °C, typ.	1.3 V				
T _J max.	175 °C				
I _R at V _R at 175 °C	1.3 μΑ				
Q _C (V _R = 400 V)	17 nC				
Package	TO-220AC 2L				
Circuit configuration	Single				

FEATURES

- · Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V_F and efficiency by thin wafer technology



- Positive V_F temperature coefficient for easy paralleling
- · Virtually no recovery tail and no switching losses
- · Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- · MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters

MECHANICAL DATA

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating

Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102 Mounting torque: 10 in-lbs maximum

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		650	V	
Continuous forward current	I _F ⁽¹⁾	T _C = 146 °C (DC)	6	А	
Continuous forward current	I _F ⁽²⁾	T _C = 153 °C (DC)	6	A	
DC blocking voltage	V_{DC}		650	V	
Repetitive peak forward current	I _{FRM}	T_C = 25 °C, f = 50 Hz, square wave, DC = 25 %	28	Α	
Non-repetitive peak forward surge current	I _{FSM}	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	42	۸	
Non-repetitive peak forward surge current		$T_C = 110$ °C, $t_p = 10$ ms, half sine wave	40	Α	
	D (1)	T _C = 25 °C	50	w	
Davier dissination	P _{tot} ⁽¹⁾	T _C = 110 °C	22		
Power dissipation	P _{tot} (2)	T _C = 25 °C	65		
		T _C = 110 °C	28		
I ² t value	∫i ² dt	T _C = 25 °C	9	A2-	
		T _C = 110 °C	8	A ² s	
Operating junction and storage temperatures	T _J ⁽³⁾ , T _{Sta}		-55 to +175	°C	

Notes

- Based on maximum Rth
- Based on typical R_{th} The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta JA}$



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
		I _F = 6 A	-	1.3	1.5		
Forward voltage	V_{F}	I _F = 6 A, T _J = 150 °C	-	1.50	1.75	V	
		I _F = 6 A, T _J = 175 °C	-	1.58	-		
		$V_R = V_R$ rated	-	0.2	35		
Reverse leakage current	I _R	$V_R = V_R$ rated, $T_J = 150$ °C	-	0.8	75	μΑ	
		V _R = V _R rated, T _J = 175 °C	-	1.3	-		
Total capacitance	С	V _R = 1 V, f = 1 MHz	-	255		pF	
		V _R = 400 V, f = 1 MHz	-	27	-	PΓ	
Total capacitive charge	Q _C	V _R = 400 V, f = 1 MHz	-	17	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS (T _A = 25 °C unless otherwise specified)							
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNIT						
Thermal resistance, junction-to-case	R _{thJC}		-	2.3	3.0	°C/W	
Marking device	3C06ET07T						

1000

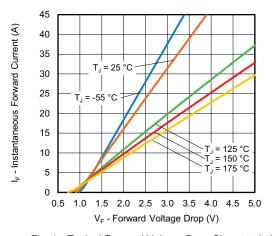


Fig. 1 - Typical Forward Voltage Drop Characteristics

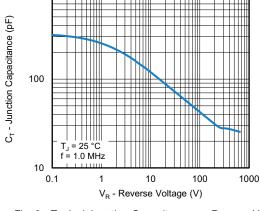


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

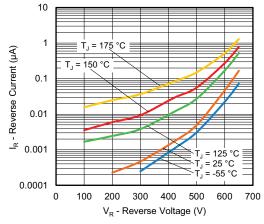


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

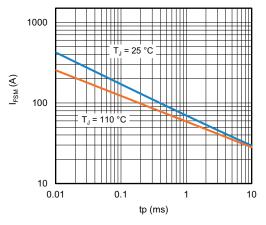


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)



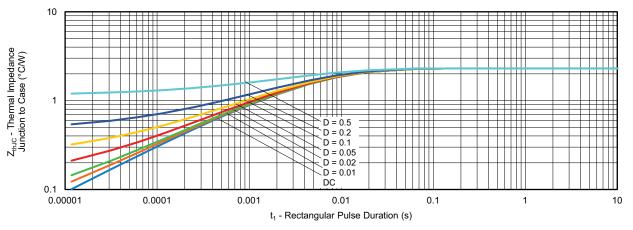


Fig. 5 - Typical Thermal Impedance Z_{thJC} Characteristics

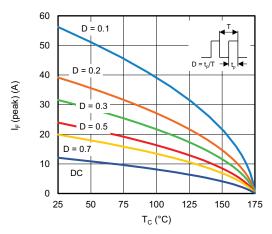


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature

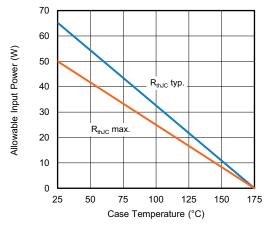


Fig. 7 - Forward Power Loss Characteristics

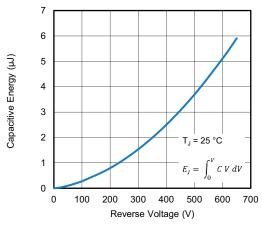


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

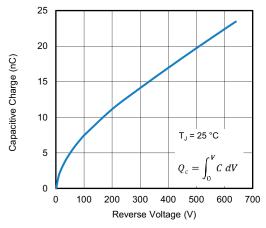
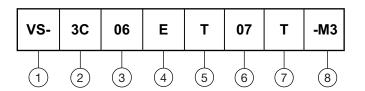


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - 3C = SiC diode, Generation 3

3 - Current rating (06 = 6 A)

- E = single diode

5 - Package TO-220

Voltage rating: (07 = 650 V)

7 - T = true 2 pin

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

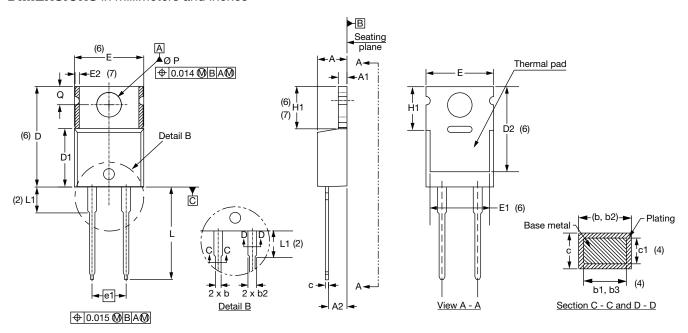
ORDERING INFORMATION		
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION
VS-3C06ET07T-M3	50 / tube	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96069</u>					
Part marking information	www.vishay.com/doc?95391				



TO-220AC 2L

DIMENSIONS in millimeters and inches



CVMPOL	SYMBOL MILLIMETERS INCHES		NOTES		
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOIES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
E	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIN	MILLIMETERS		INCHES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
e1	4.88	5.28	0.192	0.208		
H1	5.84	6.86	0.230	0.270	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- $^{(7)}$ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC® TO-220, except D2, where JEDEC® minimum is 0.480"



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